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# FOR USE BY ELECTRICIANS OVERSEAS :

**最新トランジスタ規格表** (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T <sub>b</sub> =25°C)					電気的特性 (T <sub>b</sub> =25°C)										備考	
				V <sub>ceo</sub> (V)	V <sub>ceo</sub> (V)	I <sub>c</sub> (mA)	P <sub>c</sub> (mW)	T <sub>j</sub> (°C)	I <sub>ceo</sub> 最大値 (μA)	直流又はパルスI <sub>BE</sub>		バイアス		h <sub>FE</sub>	h <sub>FE</sub> h <sub>FE</sub> * (Ω)	h <sub>FE</sub> h <sub>FE</sub> * (×10 <sup>-4</sup> )	h <sub>FE</sub> h <sub>FE</sub> * (μS)	f <sub>αb</sub> f <sub>r</sub> * (Mc)		C <sub>ob</sub> (pF)
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I<sub>CBO</sub> MAXIMUM VALUE AND V<sub>CB</sub> VALUE (CRITERIA FOR MEASURING I<sub>CBO</sub>)
- 7 STANDARD VALUE OF DC/PULSE h<sub>FE</sub> AND V<sub>CE</sub>, I<sub>C</sub> (CRITERIA FOR MEASURING DC/PULSE h<sub>FE</sub>)
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V<sub>CB</sub>, I<sub>E</sub> (CRITERIA FOR MEASURING h PARAMETERS)

- \* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f<sub>αb</sub> OF RF CHARACTERISTIC, EXCEPT IN CASE OF \* WHICH INDICATES VALUE OF f<sub>r</sub>.
- 10 C<sub>ob</sub> AND r<sub>bb'</sub> OF RF CHARACTERISTICS EXCEPT IN CASE OF \* IN r<sub>bb'</sub> COLUMN WHICH INDICATES VALUE OF h<sub>ie</sub> (real)
- 11 OUTLINE
- 12 REMARKS

: とコンプリ : COMPLEMENTARY TO .....

型名	社名	用途	構造	最大定格 (T <sub>a</sub> = 25°C)					電 気 的 特 性 (T <sub>a</sub> = 25°C)													外 形	備 考	
				V <sub>CB0</sub> (V)	V <sub>EB0</sub> (V)	I <sub>C</sub> (mA)	P <sub>C</sub> (mW)	T <sub>J</sub> (°C)	I <sub>CB0</sub> 最大値		直流又はパルス h <sub>FE</sub>			バイアス		h <sub>fe</sub> h <sub>β</sub> *	h <sub>ie</sub> h <sub>ib</sub> * (Ω)	h <sub>re</sub> h <sub>rb</sub> * (×10 <sup>-4</sup> )	h <sub>oe</sub> h <sub>ob</sub> * (μΩ)	f <sub>αβ</sub> f <sub>T</sub> * (Mc)	C <sub>ob</sub> (pF)			r <sub>bb</sub> h <sub>ie(real)</sub> * (Ω)
									V <sub>CE(V)</sub>	I <sub>C(mA)</sub>	V <sub>CE(V)</sub>	I <sub>C(mA)</sub>	V <sub>CE(V)</sub>	I <sub>E(mA)</sub>	h <sub>FE</sub> *									
★ 2SC1571	三洋	LN	Si.EP	40	5	100	200	125	0.1	18	160-960	6	1	6	-1	NF=1.5dB (f=100Hz, V <sub>CE</sub> =6V, I <sub>C</sub> =0.1mA)			100*	3	C <sub>rrs</sub> 250pS	138		
" 1572																								
" 1573	松下	AF	Si.TP	250	5	70	600	135	2	12	120	10	5	10	-3	35	300	0.4	2.7	80*	5	C <sub>rrs</sub> 60pS	165	
" 1574	東芝	LN	Si.EP	20	2	30	400	175	0.1	10	70	10	5	10	-10	G <sub>pp</sub> =15dB, NF=12dB, 4.5GHz (f=500MHz, I <sub>C</sub> =3mA)				11.5	20*	85B		
" 1575																								
" 1576	東芝	SW	Si.T	450	6	8 A	100W (T <sub>C</sub> =25°C)	150	100	450	30-150	5	1 A			t <sub>on</sub> =1μS, t <sub>off</sub> =0.8μS t <sub>rise</sub> =3μS							102	
" 1577	サンケン	"	Si.TMe	500	6	8 A	80W (T <sub>C</sub> =25°C)	150	1mA	500	30	4	3 A	12	-500					7*	55	4*	102	
" 1578	"	"	"	600	6	8 A	80W (T <sub>C</sub> =25°C)	150	1mA	600	30	4	3 A	12	-500					7*	55	4*	102	
" 1579	"	PA	"	500	6	15A	150W (T <sub>C</sub> =25°C)	150	1mA	500	20	4	5 A	12	-500					7*	80	3*	102	
" 1580	"	"	"	600	6	15A	150W (T <sub>C</sub> =25°C)	150	1mA	600	20	4	5 A	12	-500					7*	80	3*	102	
" 1581	東芝	PA	Si.EP	65		7 A	80W (T <sub>C</sub> =25°C)	175	3mA	300	30	10	5 A			P <sub>o</sub> =50W (f=30MHz, V <sub>CE</sub> =28V, P <sub>i</sub> =2W)							223	
" 1582	"	"	"	65		13A	140W (T <sub>C</sub> =25°C)	175	6mA	300	30	10	10A			P <sub>o</sub> =100W (f=30MHz, V <sub>CE</sub> =28V, P <sub>i</sub> =8W)							223	
" 1583	三菱	Diff.LN	"	50	5	100	200/unit	125	0.1	25	250-1200	6	-1	6	-1	ΔV <sub>BE</sub> =10mVmax h <sub>FE</sub> */h <sub>FE</sub> 大=0.8-1.0				100*	3.0		274B	2素子 複合
" 1584	サンケン	PA	Si.TMe	150	6	15A	150W (T <sub>C</sub> =25°C)	150	1mA	150	60	4	5 A	12	-500	t <sub>on</sub> =1.3μS t <sub>rise</sub> =2μS	t <sub>f</sub> =1μS		10*	110	10*	102	2SA907 とコンパリ	
" 1585	"	"	"	200	6	15A	150W (T <sub>C</sub> =25°C)	150	1mA	200	60	4	5 A	12	-500	t <sub>on</sub> =1.3μS t <sub>rise</sub> =2μS	t <sub>f</sub> =1μS		10*	110	10*	102	2SA908 とコンパリ	
" 1586	"	"	"	250	6	15A	150W (T <sub>C</sub> =25°C)	150	1mA	250	60	4	5 A	12	-500	t <sub>on</sub> =1.3μS t <sub>rise</sub> =2μS	t <sub>f</sub> =1μS		10*	110	10*	102	2SA909 とコンパリ	
" 1587	三菱	"	Si.EP	45	4.5	3 A	50W (T <sub>C</sub> =25°C)	175	1mA	300	50	25	200			P <sub>o</sub> =30W (f=28MHz, V <sub>CE</sub> =23V, P <sub>i</sub> =6W)							224	
" 1588	日電	"	Si.E	36	4	300	1.7W (T <sub>C</sub> =25°C)	125	100	300	55	10	100	10	-30	P <sub>o</sub> =0.4W (f=225MHz, V <sub>CE</sub> =12V, P <sub>i</sub> =10mW)				900*	<10		167B	
" 1589	"	"	"	36	4	700	2.5W (T <sub>C</sub> =25°C)	150	100	300	15-200	10	300	10	-50	P <sub>o</sub> =1.5W (f=225MHz, V <sub>CE</sub> =12V, P <sub>i</sub> =0.2W)				700*	<15		167B	
" 1590	"	"	"	36	4	1.2A	13.5W (T <sub>C</sub> =25°C)	175	1mA	300	15-200	10	500	10	-300	P <sub>o</sub> =6.5W (f=225MHz, V <sub>CE</sub> =12V, P <sub>i</sub> =0.7W)				400*	<25		226	
" 1591	"	"	"	36	4	2.5A	30W (T <sub>C</sub> =25°C)	175	2mA	300	15-200	10	1 A	10	-500	P <sub>o</sub> =15.5W (f=225MHz, V <sub>CE</sub> =12V, P <sub>i</sub> =4W)				250*	<50		226	
" 1592	"	"	"	30	3	100	3.5W (T <sub>C</sub> =25°C)	200	0.1	20	100	10	50	10	-50					2700*	C <sub>rr</sub> 1		129	
" 1593	"	RF	"	40	3	150	4.375W (T <sub>C</sub> =25°C)	200	50	200	15-200	10	70	10	-70					2000*	2.5		129	
" 1594	"	PA	"	35	3	200	7W (T <sub>C</sub> =25°C)	200	10	200	60	10	100	10	-100	G <sub>μ</sub> 10.5dB (f=1GHz, V <sub>CE</sub> =15V, I <sub>C</sub> =100mA)				2500*	C <sub>rr</sub> 2.8		129	
" 1595	"	"	"	35	3	300	7W (T <sub>C</sub> =25°C)	200	10	200	60	10	100	10	-100	G <sub>pp</sub> =3.5dB (f=2.3GHz, V <sub>CE</sub> =18V, P <sub>i</sub> =30dBm)				2500*	C <sub>rr</sub> 2.8		129	
★ 1596	富士通	RF	Si.EP	150	5	50	450	175	1	140	60	5	10	5	-10	t <sub>on</sub> <1μS, t <sub>off</sub> <10μS t <sub>rise</sub> <9.5μS				130*	2	70*	55C	
" 1597	"	AF	"	150	5	50	450	175	1	140	150	5	10							130*	20	70*	244	
" 1598																								
" 1599																								
" 1600	日電	RF	Si.E	40	3	250	4.375W (T <sub>C</sub> =25°C)	200	100	200	15-200	10	100	10	-100	P <sub>osc</sub> =28.5dBm (f=1.7GHz, V <sub>CE</sub> =-18V)				2000*	C <sub>rr</sub> 3		315	